Antoine Goullet

List of Publications by Year in descending order

32 papers	822 citations	394421 19 h-index	477307 29 g-index
32 all docs	32 docs citations	32 times ranked	832 citing authors

#	Article	IF	Citations
1	A comparative study of oxygen/organosilicon plasmas and thin SiOxCyHz films deposited in a helicon reactor. Thin Solid Films, 2000, 359, 188-196.	1.8	124
2	Diagnostics in helicon plasmas for deposition. Plasma Sources Science and Technology, 1997, 6, 147-156.	3.1	92
3	Inorganic to organic crossover in thin films deposited from O2/TEOS plasmas. Journal of Non-Crystalline Solids, 2000, 272, 163-173.	3.1	64
4	Ellipsometry and Raman study on hydrogenated amorphous carbon (a-C:H) films deposited in a dual ECR-r.f. plasma. Thin Solid Films, 1999, 352, 41-48.	1.8	37
5	Nitrogen doping on NiO by reactive magnetron sputtering: A new pathway to dynamically tune the optical and electrical properties. Applied Surface Science, 2017, 409, 77-84.	6.1	37
6	Optical characterization of hydrogenated amorphous carbon (a-C:H) thin films deposited from methane plasma. Thin Solid Films, 2000, 364, 144-149.	1.8	35
7	In situ spectroscopic ellipsometry study of TiO2 films deposited by plasma enhanced chemical vapour deposition. Applied Surface Science, 2013, 283, 234-239.	6.1	34
8	In situ ellipsometry and infrared analysis of PECVD SiO2 films deposited in an O2/TEOS helicon reactor. Journal of Non-Crystalline Solids, 1997, 216, 48-54.	3.1	31
9	Structural, morphological and electrical properties of nickel oxide thin films deposited by reactive sputtering. Applied Surface Science, 2015, 357, 838-844.	6.1	31
10	Analysis of Low-k Organosilicon and Low-Density Silica Films Deposited in HMDSO Plasmas. Plasmas and Polymers, 2002, 7, 341-352.	1.5	29
11	Quantitative infrared analysis of the stretching peak of SiO2films deposited from tetraethoxysilane plasmas. Journal of Applied Physics, 1993, 74, 6876-6882.	2.5	27
12	Carbon nanotubes and nanostructures grown from diamond-like carbon and polyethylene. Applied Physics A: Materials Science and Processing, 2001, 73, 765-768.	2.3	27
13	Structure and properties of silicon oxide films deposited in a dual microwave-rf plasma reactor. Thin Solid Films, 2001, 384, 230-235.	1.8	25
14	Unravelling local environments in mixed TiO2â€“SiO2 thin films by XPS and ab initio calculations. Applied Surface Science, 2020, 510, 145056.	6.1	23
15	In situ deposition and etching process of a-C:H:N films in a dual electron cyclotron resonanceâ€“radio frequency plasma. Diamond and Related Materials, 2000, 9, 573-576.	3.9	22
16	Electrical properties of low-dielectric-constant films prepared by PECVD in O2/CH4/HMDSO. Materials Science in Semiconductor Processing, 2002, 5, 279-284.	4.0	22
17	Conception of optical integrated circuits on polymers. Microelectronics Journal, 2006, 37, 421-427.	2.0	22
18	Process- and optoelectronic-control of NiOx thin films deposited by reactive high power impulse magnetron sputtering. Journal of Applied Physics, 2017, 121, .	2.5	21

#	Article	IF	Citations
19	Mechanisms Involved in the Conversion of ppHMDSO Films into SiO2-Like by Oxygen Plasma Treatment. Plasma Processes and Polymers, 2006, 3, 365-373.	3.0	20
20	Structural and Optical Properties of PECVD TiO₂-SiO₂Mixed Oxide Films for Optical Applications. Plasma Processes and Polymers, 2016, 13, 918-928.	3.0	17
21	Comparative Study of Films Deposited from HMDSO/O2 in Continuous Wave and Pulsed rf Discharges. Plasma Processes and Polymers, 2007, 4, S287-S293.	3.0	13
22	TiO₂â€“SiO₂ nanocomposite thin films deposited by direct liquid injection of colloidal solution in an O₂/HMDSO low-pressure plasma. Journal Physics D: Applied Physics, 2021, 54, 085206.	2.8	12
23	Optical properties of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Ti</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:mo>,</mml:mo><mml:mi mathvariant="normal">O</mml:mi><mml:mn>2</mml:mn></mml:mrow></mml:math> solid solutions. Physical Review B, 2017, 95, .	3.2	9
24	Influence of Ion Bombardment and Annealing on the Structural and Optical Properties of TiO_x Thin Films Deposited in Inductively Coupled TTIP/O₂ Plasma. Plasma Processes and Polymers, 2009, 6, S741.	3.0	8
25	Ultra wide band frequency characterization of integrated TiTaO-based metalâ€“insulatorâ€“metal devices. Journal of Applied Physics, 2011, 110, 044110.	2.5	8
26	A unified analytical and scalable lumped model of RF CMOS spiral inductors based on electromagnetic effects and circuit analysis. Solid-State Electronics, 2011, 61, 38-45.	1.4	7
27	SiCN:H thin films deposited by MWâ€PECVD with liquid organosilicon precursor: Gas ratio influence versus properties of the deposits. Plasma Processes and Polymers, 2020, 17, 1900138.	3.0	6
28	Hybrid approaches coupling solâ€“gel and plasma for the deposition of oxide-based nanocomposite thin films: a review. SN Applied Sciences, 2021, 3, 1.	2.9	6
29	Influence of synthesis conditions on optical and electrical properties of CaTiO3:Pr3+ thin films deposited by radiofrequency sputtering for electroluminescent device. Surface and Coatings Technology, 2011, 205, S250-S253.	4.8	5
30	Nearâ€field scanning microscopy and physicoâ€chemical analysis versus time of SiCN:H thin films grown in Ar/NH3/TMS gas mixture using MWâ€Plasma CVD at 400â€‰Â°C. Plasma Processes and Polymers, 2018, 15, 1800066.	3.0	5
31	Ion impingement effect on the structure and optical properties of Ti x Si 1â^' x O 2 films deposited by ICPâ€PECVD. Plasma Processes and Polymers, 2019, 16, 1900034.	3.0	3
32	Comparison of Electrical Behavior of GaN-Based MOS Structures Obtained by Different PECVD Process. Materials Science Forum, 0, 711, 228-232.	0.3	0